

**IN THE CLAIMS:**

Amend claims 2, 6 and 14 and cancel claims 1 and 7-13 without prejudice or admission as shown in the following listing of claims, which replaces all previous listings and versions of claims.

1. (canceled).
2. (currently amended) ~~A voltage detecting circuit according to claim 1; wherein A voltage detecting circuit, comprising:~~  
a first terminal connected to a positive pole of a battery;  
a second terminal connected to a negative pole of the battery;  
a voltage dividing circuit that divides a voltage across the battery;  
a reference voltage circuit that generates a reference voltage;  
a comparator that compares outputs of the reference voltage circuit and the voltage dividing circuit and outputs a comparison signal;  
a first output circuit connected between the first terminal and the second terminal for outputting a first output signal on the basis of the comparison signal output by the comparator;

an output terminal for outputting the first output signal; and

a second output circuit connected between the output terminal and one of the first and second terminals for outputting a second output signal that changes in value on the basis of a first signal and a second signal at the first terminal and the second terminal, respectively, the second output circuit comprises comprising a depletion-type n-channel MOS transistor and a depletion-type p-channel MOS transistor connected in series between the output terminal and one of the first terminal and the second terminal; and wherein the first signal at the first terminal is input to a gate electrode of the depletion-type p-channel MOS transistor, and the second signal at the second terminal is input to a gate electrode of the depletion-type n-channel MOS transistor.

3. (previously presented) A voltage detecting circuit according to claim 2; wherein the first output circuit comprises an enhancement-type n-channel MOS transistor and an enhancement-type p-channel MOS transistor connected in series between the first terminal and the second terminal; and wherein a signal based on the comparison signal output by the comparator is input to gate electrodes of the enhancement-type p-channel MOS transistor and the enhancement-type n-channel MOS transistor, and absolute values of threshold voltages of

the depletion-type n-channel MOS transistor and the depletion-type p-channel MOS transistor are larger than absolute values of threshold voltages of the enhancement-type n-channel MOS transistor and the enhancement-type p-channel MOS transistor.

4. (previously presented) A voltage detecting circuit according to claim 2; wherein the first terminal is connected to the gate electrode of the depletion-type p-channel MOS transistor and the second terminal is connected to the gate electrode of the depletion-type n-channel MOS transistor.

5. (previously presented) A voltage detecting circuit according to claim 3; wherein the comparison signal is input to gate electrodes of the enhancement-type p-channel MOS transistor and the enhancement-type n-channel MOS transistor.

6. (currently amended) A voltage detecting circuit according to claim ± 2; wherein the first output circuit comprises two enhancement mode MOS transistors connected in series between the first and second terminals.

7.-13. (canceled).

14. (currently amended) ~~A voltage detecting circuit according to claim 13; wherein A voltage detecting circuit, comprising: input terminals; an output terminal; a reference~~

voltage generator for generating a reference voltage; a comparator for comparing a voltage across the input terminals with the reference voltage and outputting a comparison signal; a first output circuit connected between the input terminals for outputting a first signal to the output terminal on the basis of the comparison signal; and a second output circuit connected between the output terminal and one of the input terminals for varying a resistance value between the output terminal and the one of the input terminals based on the voltage across the input terminals; wherein the first output circuit comprises two enhancement mode MOS transistors connected in series between the input terminals, the two enhancement mode MOS transistors have opposite polarities, an output of the comparator is connected to gate electrodes of the two enhancement mode MOS transistors, and the second output circuit comprises two depletion mode MOS transistors connected in series between the output terminal and one of the input terminals.

15. (previously presented) A voltage detecting circuit according to claim 14; wherein the two depletion mode MOS transistors have opposite polarities.

16. (previously presented) A voltage detecting circuit according to claim 15; wherein a gate electrode of one of the depletion mode MOS transistors is connected to one of the input terminals, and a gate electrode of the other depletion mode MOS transistor is connected to another one of the input terminals.

17. (previously presented) A voltage detecting circuit according to claim 16; wherein absolute values of threshold voltages of the depletion mode MOS transistors are larger than absolute values of threshold voltages of the enhancement mode MOS transistors.